



Docket No. 740819-610

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

Michikazu Matsumoto et al.

Serial No. 09/922,804

Filed: August 7, 2001

For: ELECTRODE STRUCTURE AND
METHOD FOR FABRICATING THE
SAME

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Group Art Unit: 2826

Examiner: Fazli Erdem

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231, on 3/24/2003

W SPRADLIN

PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Final Office Action dated December 31, 2002, and the attached Request for Continued Examination, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 1-10 as follows. Please note the claims are presented below in their amended form. Furthermore, the claims are presented as an attachment to the amendment where the amendments are shown using the conventional technique of bracketing and underlining. Applicants have endeavored to maintain consistency

between the marked-up and amended versions of the claims. However, should there be

discrepancy, the clean version prevails.

1. (Amended) A gate electrode structure comprising:
a silicon-containing film formed on a gate insulating film and containing silicon as a principal constituent;
a barrier metal layer of titanium nitride rich in titanium as compared with a